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## C oherent O scillations and G iant E dge M agnetoresistance in Singly C onnected Topological Insulators

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The topological insulators have a gap in the bulk but extended states at the edge that can carry current. We study a geometry in which such edge states will manifest them selves through periodic oscillations in them agnetoconductance of a singly connected sample coupled to leads through narrow point contacts. The oscillations occur due to quantum interference of helical edge states of electrons traveling along the circum ference of the sample, and have a period of  $B = h=eA_e$ , where  $A_e$  is the electrive area enclosed by the edge states of the sample. Our calculation indicates the possibility of a large change in the magnetoresistance at small B, term ed giant edge magnetoresistance, which can have potential for application. The zero eld conductance also exhibits oscillations as a function of the Ferm i energy due to interference between edge states. The amplitude of the oscillations is governed by, and therefore can be used to investigate, the transverse width of the edge channels.

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Topological insulators di er from ordinary insulators in having a pair of extended helical edge states, which results in quantum spin Hall (QSH) e ect [1, 2, 3]. Several candidates for topological insulators have been proposed, and a non-zero conductance has been measured experimentally in the "inverted"-band sem iconductor HqTe/CdTe quantum well in a band insulating region.[3] M ore experiments are beginning to explore the edge and surface state properties in topological insulators.[4, 5, 6, 7, 8] A direct observation of extended edge states would be in portant to establish the physics of topological insulators, and one may ask if they can also exhibit other interesting phenom ena. W e dem onstrate that an e ective one-dimensional ring is formed between two consecutive scatterers, which leads to Aharonov{ Bohm (AB) oscillations in conductance. An observation of such oscillations in a singly connected geometry will constitute a direct observation of edge transport. Such oscillations are analogous to sim ilar oscillations in singly connected quantum Hallsystems [9, 10, 11], but with an in portant di erence: in the present case, the oscillations occurat very smallm agnetic elds. O ur results also indicate the possibility of a "giant edge m agnetoresistance" (GEMR), which is insensitive to the geometry of the device and m ay have potential for practical application.

W e study here the device shown in FIG 1, which consists of a two-dimensional strip of a topological insulator on which two quantum point contacts (QPCs) have been patterned thorough gates (shaded regions in FIG. 1). The QPCs de ne a saddle shaped con ning potential, whose height can be controlled by a gate voltage. An effective disk of area  $A = R^2$  (R is the radius of the disk) is form ed in the center. An AB e ect in the device can be expected intuitively because a topological insulator



FIG.1: Schem atic of the geom etry studied in this manuscript, which consists of a disk connected to two reservoirs through two quantum point contacts. Red and blue lines indicate the chiral edge channels of spin up and down electrons, with arrows indicating the direction of their motion. In our calculations, we take the following parameters: width W = 500nm, length L = 1030nm; the slit width d of the quantum point contacts is taken as a variable.

possesses a pair of independent gapless edge states of different spins moving in opposite directions, each forming an ideal one-dimensional loop around the disk. The two edge states are independent because no backscattering is allowed at a given sample edge even in the presence of weak time-reversal invariant disorder. We note here that spin is not a good quantum number in topological insulators because of spin orbit coupling. In the absence of a magnetic eld, the actual edge states are eigenstates of the time reversal operator; their characterization as spin up and down is not precisely correct, and the word \spin" below is to be viewed more generally as the quantum num ber denoting the two states of a K ram ers doublet. The e ect of magnetic eld, which breaks time reversal symmetry, is complicated. In our considerations below we assume that the magnetic eld is su ciently weak that the Zeeman term can be neglected; in that limit, the eld does not open any gap in the spectra for the edge states, as discussed in detail in Ref. [12].

In the remainder of the article we study this geometry quantitatively. W e will assume that the weak magnetic eld B is norm al to the plane. Following Ref. [10] we consider a spin-up (or spin-down) electron travelling from the left hand side (LHS) in FIG. 1. At the LHS junction it splits into two partial waves: one is transm itted through the QPC into the disk with am plitude t, and the other is transmitted across the QPC with an amplitude r causing a backscattering. W e denote the wave function am plitudes in the upper edge and low er edge, right after the LHS junction, by  $u_1$  and  $d_1$ , respectively. The corresponding amplitudes in the vicinity of RHS junction are  $u_2 = u_1 \exp[i = 2]$  and  $d_2 = d_1 \exp[i = 2]$ , where , \_ = h=e a fundam ental unit of m ag-= 2 = 0 + 1netic ux, =  $R_e^2 B$  is the magnetic ux threading the e ective one-dimensional loop with an e ective ra $dius R_e$  , and is the phase acquired by the wave function traveling along the loop  $= 2 kR_e$  . A partial wave goes through the RHS slit with an amplitude  $t^0$ and across the slit with an amplitude  $r^0$ . To simplify the problem, we assume identical relection and transmission am plitudes for the two slits,  $t = t^0$  and  $r = r^0$ . U sing the theory of multi-scattering processes [13] it then follows that the total transm ission for spin-up electron through the slit A and B is given by

$$T''(B) = \frac{T_0^2}{T_0^2 + 4(1 - T_0)\cos^2\frac{+}{2}}:$$
 (1)

Here  $T_0 = t^2$  is the transm ission coe cient of an electron through a slit, and  $_0 = \arg(rr^0)$ : Resonant tunneling occurs for  $\cos \frac{+}{2} = 0$ , i.e., T''(B) = 1 for any  $T_0$ . The transm ission coe cient for a spin-down electron  $T^{\#}(B)$ ; which is the time reversal counterpart of spin-up electron at B eld, is given by  $T^{\#}(B) = T''(B)$ . A coording to the Landauer-Buttiker form ula,[14, 15] the total conductance is

G (B) = 
$$\frac{e^2}{h}$$
 [T " (B) + T <sup>#</sup> (B)]: (2)

The AB oscillations in the conductance G as a function of the magnetic ux through the disk are therefore expected to be symmetric with respect to the direction of the magnetic eld.

To make further progress, we undertake a numerical calculation for the specic case of an inverted"-band HgTe/CdTe heterojunction. We consider with the elective H am iltonian for HgTe/CdTe quantum well[2]

$$H = \begin{array}{c} h(k) & 0 \\ 0 & h(k) \end{array} ; \qquad (3)$$



FIG. 2: (a) M agnetoconductance G for several energies in the band gap. (b) The locations of the energies for the curves in panel (a). (c) C onductance G<sup>"</sup> as a function of the Ferm i energy at zero m agnetic eld (B = 0). A llcalculations assume point contact constriction width of d = 40nm.

where, in the spin-up sector,  $h(k) = D k^2 + A (k_x + k_y + y) + (M - B k^2)_z$ ; and  $k = (k_x; k_y)$  is the wave vector in two dimension, k is the Paulimatrix vector. A, B, D and M are sample speci c parameters, and are functions of the thickness of the quantum well; here we take A = 364:5m eV nm<sup>2</sup>, B = 686m eV nm<sup>2</sup>, D = 512m eV nm<sup>2</sup>, M = 10m eV. In the spin-down sector h (k) is the time reversal counterpart of h(k). The existence of edge states in thism odel has been discussed previously.[12, 16]

To determ ine the conductance through the disk subjected to a perpendicular and weak eld B, we use the K eldysh G reen function technique to calculate the transm ission coe cients T num erically in the Landauer-Buttiker form alism [13]. For this purpose, we use a tight-binding m odel that reproduces the H am iltonian in Eq. (3) in the continuum limit, and include them agnetic eld through the substitution k ! k  $\stackrel{e}{\sim}$  A (A is the vector potential). In the present work, m ore 400 200 lattice sites and the lattice space a = 2.5nm were used in the calculation, and the lattice size e ects are vanishingly sm all, so all results reported here re ect the continuum limit.

FIG.2 shows the conductance for several Ferm i energies, whose locations in the band structure are illustrated in FIG. 2(b). The conductance exhibits periodical oscillations in B, with the period determ ined by the magnetic ux. Form ost param eters, the maxim alvalue of the conductance does not reach  $2e^2$ =h because T " (B) and T  $^{\#}$  (B) in generaldo not satisfy the resonance condition simultaneously. A new feature is the rapid oscillations in the conductance at B = 0 as a function the Ferm ienergy  $E_{f}$ , as shown in FIG. 2 (c). These oscillations are caused by the phase shift 2 kRe where the dispersion of the edge state  $A^{1} 1 D^{2} = B^{2}k$ MD=B +7:46 242:5k E (k) meV (k in unit of nm<sup>1</sup>) is linear in k. The increas-



FIG. 3: The magnetoconductance of a single spin channel for several widths d of the quantum point contacts, obtained num erically for the sample of Fig. 1. The black curves are ts using Eq. (1). Sm aller d produces sm aller t (CHECK) and hence larger oscillation amplitude. The insert shows the relation between  $T_0$  and d. The period is independent of d. A ll curves are evaluated for  $E_f = 0.5m$  eV.

ing oscillation amplitude re ects that the spatial distribution of edge state is dependent on the Fermienergy. According to Zhou et al.[12] the spatial distribution of the edge state near the boundary has the  $(y) = (e^{y=1} e^{y=2}) = \frac{1}{2} + \frac{2}{2}$  $\frac{2}{+}$  where form 317 = (240 + E) and <sub>2</sub> 317=(13:4 E) nm (E 1 in units of  $m \in V$ ) near the crossing point k = 0 for the param eters adopted in this paper. Because we typically have  $_1 << _2$ , the spatial distribution of the edge state is determined dominantly by 2. Thus the edge state becom es wider with increasing energy, ultim ately evolving into a bulk state when E 13:4m eV. Correspondingly, the transm ission coe cients decreases and the oscillation am plitude increases according to Eq.(1).

FIG.3 shows the dependence of oscillations on the slit width d. The solid lines are the best ts from Eq.(1) with three adjustable parameters  $T_0$ ,  $R_e$  and :The e ective radius  $R_e = 2_0 = B_0$  can be deduced from the period B<sub>0</sub> of the oscillation; its ratio to the radius of the disk is R<sub>e</sub> =R 0:95; which re ects the nite width of an edge state near the boundary of the disk. The inset in FIG.3 shows how  $T_0$  depends on the slit width d. A sexpected,  $T_0$  vanishes for d=  $_2 << 1$  and approaches unity for  $d=_2 >> 1$ . C onductance oscillations are suppressed in both lim its; in particular, for  $d=_2 >> 1$  it has the universal value  $2e^2 = h$  [1, 2] and displays no magnetoresistance. The AB oscillations occur only when the slit width is comparable to the spatial distribution of edge state. The num erical results are in good agreem ent with Eq.(1) in the rst one or two periods, but exhibit an increasing deviation for a larger eld B, which m ay originate from the neglect, in our ts, of the dependence of the energy dispersion of the edge states on magnetic eld



FIG. 4: Panels (a) and (b) show the local current density distributions on the sample of Fig.1 for magnetic elds B at a peak and a valley of the magnetoresistance, which correspond to maximum transmission and maximum rejection, respectively. The current rejection is totally suppressed in (a). The panels (c) and (d) show the corresponding local density of states distributions. The calculation assumes the parameters d = 30 nm and E = 0.5 meV.

(we use the B = 0 dispersion when thing the numerical data).

The quasi-one dimensional quantum interference behavior can be further illustrated by plotting the spatial pro le of local current and the local density of states in a nonequilibrium situation [17], where Ferm i surface is slightly higher in the left lead so that the electrons ow from left to right. Current ow patterns for the up spin sector are shown in Figs. 4(a) and 4(b). The current ows only along the boundary of the device with de nite chirality (see FIG.1). At the resonance transmission  $T_0 = 1$ , the backward current relection at QPC A is totally suppressed, which corresponds to a peak in the magnetoresistance oscillations. The maximum re ection is observed at the valley of the oscillations. W hen a resonance transm ission occurs, the maximum of local density of states is found in the central disk edge while, at m inimum transmission, the maximum local density of states is observed in the term inals.

The feasibility of the observations of the predicted m agnetoresistance oscillations depends in part on how sensitive their amplitude is to the ever present disorder. G iven that time reversal invariant disorder does not cause any backscattering between two spin channels at the same edge[1, 20, 21], one m ight expect that it also does not a ect the coherent m agnetoresistance oscillations. We study the e ect of disorder by introducing disorder as a random on-site energy with a uniform distribution within [ w=2;w=2]. The results, displayed in F IG .5(a), demonstrate that disorder dim inishes the am - plitude of oscillations while enhancing the average conductance. The reduction of the coherent oscillations orig-



FIG. 5: (a). Conductance oscillations in the spin up sector as a function of disorder. The oscillations gradually atten but electron tunnelling through the slit is signi cantly enhanced with increasing disorder strength. (b) The disorder dependence of transm ission coe cient through a single QPC  $T_0$  for three di erent spatial distributions of disorders. Red line - disorder is distributed over the entire device. B lue line - disorder is distributed only in the vicinity of the QPC slit. P ink line -no disoder in the vicinity of the QPC slit. The inset in (b) shows the variance of the period of magnetic eld as a function of the disorder strength for two di erent spatial distribution of disorder. A veraging is perform ed over 200 disorder sam ples; the param eters are chosen as d = 40nm, E = 5.5m eV.

inates from an impurity con guration dependent phase shift in Eq. (1); the disorder averaging over the phase shift sm ears the quantum interference, com pletely suppressing it when the variance of is comparable with . It is noteworthy that the AB oscillations survive up to quite large disorder. For com parison, the hopping m atrix element in Eq.(3) ist =  $D = a^2 \prime 82 \text{ m eV}$ , and num erical results indicate that the oscillation is alm ost suppressed when the on-site disorder ! t. The enhancem ent of the average conductance is surprising at st sight (see FIG. 5(b)), but we attribute it to a squeezing the spatial distribution of the edge states by disorder. Such squeezing can also be seen in the slight decreasing of the oscillation period of the conductance with large disorder strength as the elective radius R  $_{\rm eff}$  =  $2_{0}=B_{0}$  (see the insert in FIG.5(b).). A lso the disorder around the slit can increase the tunneling probability as the higher disorder can close the energy gap (caused by the nite size of the slit) near the Ferm i surface [18]. O f course, even stronger

disorder leads to the Anderson localization, and the edge states will be destroyed [19, 22, 23], resulting in a lack of conductance.

A llour preceding discussion assum as strictly zero tem – perature. Scattering between the spin up and spin down edges becomes possible at nonzero tem peratures due to inelastic scattering involving phonons, which is believed to cause the deviation from perfect quantization in the experiments of R ef. [3]. The AB oscillations discussed above will be observable only for disks with perimeters less than the phase coherence length of the edge states.

In conclusion, we have studied theoretically a geometry in which the edge states of topological insulators are predicted to produce coherent oscillations in the magnetoconductance due to Aharonov-Bohm interference. This physics also produces a giant edge magnetoresistance in a weak edd; FIG.2 shows that the conductance may change by an order of magnitude for a tiny eld B 0.01T. If con med by experiments, this may be of practical interest. The giant edge magnetoresistance can be controlled by varying the slit width d and the size of the disk. We have also studied its sensitivity to disorder, and found that it persists for quite large disorder. The amplitude of AB oscillations also contains information about the transverse spatial extent of the edge channels.

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